

L Number	Hits	Search Text	DB	Time stamp
-	2	jp-07235672\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 08:43
-	2	jp-09270512\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/29 18:48
-	2	jp-10150191\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/29 18:48
-	10	jp-6350071\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/29 18:49
-	0	jp-036350071\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/29 18:49
-	0	jp-36350071\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/29 18:50
-	547	kawashima.in. and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/29 18:50
-	7	(kawashima.in. and gate) and trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/29 18:51
-	94	kawashima.in. and "1988" and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/29 18:54
-	13821	trench.ti,ab. and (semiconductor or field adj effect).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/29 19:38
-	619	257/329	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/29 19:38
-	897	257/330	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/29 19:38
-	489	257/331	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/29 19:38

-	444	257/332	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/29 19:38
-	133	257/905	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/29 19:41
-	120	438/212	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/29 19:41
-	373	438/259	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/29 19:41
-	1505	438/270	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/29 19:42
-	373	438/271	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/29 19:42
-	292	438/589	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/29 19:42
-	345	438/587	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/29 19:42
-	227	438/588	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/29 19:43
-	4220	257/329 or 257/330 or 257/331 or 257/332 or 257/905 or 438/212 or 438/259 or 438/270 or 438/271 or 438/589 or 438/587 or 438/588	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 16:16
-	228	(( (257/329 or 257/330 or 257/331 or 257/332 or 257/905 or 438/212 or 438/259 or 438/270 or 438/271 or 438/589 or 438/587 or 438/588) and @rlad<19990918) and (trench or groove)) and (trench adj3 gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/29 20:05
-	189	(( (257/329 or 257/330 or 257/331 or 257/332 or 257/905 or 438/212 or 438/259 or 438/270 or 438/271 or 438/589 or 438/587 or 438/588) and @rlad<19990918) and (trench or groove)) and (trench adj2 gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 12:21
-	581	(trench or groove) and (trench adj2 gate) and semiconductor	EPO; JPO; DERWENT; IBM TDB	2001/10/30 12:23
-	809	(257/329 or 257/330 or 257/331 or 257/332 or 257/905 or 438/212 or 438/259 or 438/270 or 438/271 or 438/589 or 438/587 or 438/588) and @rlad<19990918	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 12:25

-	150	(257/329 or 257/330 or 257/331 or 257/332 or 257/905 or 438/212 or 438/259 or 438/270 or 438/271 or 438/589 or 438/587 or 438/588) and trench adj (gate or region) and (igbt or mosfet) and power adj2 (semiconductor or device)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 14:47
-	150	(257/329 or 257/330 or 257/331 or 257/332 or 257/905 or 438/212 or 438/259 or 438/270 or 438/271 or 438/589 or 438/587 or 438/588) and trench adj (gate or region) and ("igbt" or mosfet) and power adj2 (semiconductor or device)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 14:48
-	0	((257/329 or 257/330 or 257/331 or 257/332 or 257/905 or 438/212 or 438/259 or 438/270 or 438/271 or 438/589 or 438/587 or 438/588) and trench adj (gate or region) and ("igbt" or mosfet) and power adj2 (semiconductor or device)) not ((257/329 or 257/330 or 257/331 or 257/332 or 257/905 or 438/212 or 438/259 or 438/270 or 438/271 or 438/589 or 438/587 or 438/588) and trench adj (gate or region) and (igbt or mosfet) and power adj2 (semiconductor or device))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 14:48
-	2	jp-09270512\$-\$.did.	EPO; JPO; DERWENT; IBM TDB	2001/10/30 14:56
-	2	5648670.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 16:14
-	513	("257/341").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 16:14
-	483	((257/329 or 257/330 or 257/331 or 257/332 or 257/905 or 438/212 or 438/259 or 438/270 or 438/271 or 438/589 or 438/587 or 438/588) and @rlad<19990918) and (trench or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 16:17
-	280	("257/342").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 16:18
-	993	("257/401").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 16:18
-	78	("257/135").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 16:18
-	124	("257/491").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 16:18
-	73	("257/492").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 16:18

-	83	("257/493").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 16:18
-	1911	((("257/341").CCLS.) or (("257/342").CCLS.) or (("257/401").CCLS.) or (("257/135").CCLS.) or (("257/491").CCLS.) or (("257/492").CCLS.) or (("257/493").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 16:20
-	419	((("257/341").CCLS.) or (("257/342").CCLS.) or (("257/401").CCLS.) or (("257/135").CCLS.) or (("257/491").CCLS.) or (("257/492").CCLS.) or (("257/493").CCLS.)) and (trench or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 16:40
-	129	((("257/341").CCLS.) or (("257/342").CCLS.) or (("257/401").CCLS.) or (("257/135").CCLS.) or (("257/491").CCLS.) or (("257/492").CCLS.) or (("257/493").CCLS.)) and (trench or groove)) and @rlad<19990918	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 16:37
-	290	((("257/341").CCLS.) or (("257/342").CCLS.) or (("257/401").CCLS.) or (("257/135").CCLS.) or (("257/491").CCLS.) or (("257/492").CCLS.) or (("257/493").CCLS.)) and (trench or groove)) not (((("257/341").CCLS.) or (("257/342").CCLS.) or (("257/401").CCLS.) or (("257/135").CCLS.) or (("257/491").CCLS.) or (("257/492").CCLS.) or (("257/493").CCLS.)) and (trench or groove)) and @rlad<19990918)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 17:53
-	402	((("257/341").CCLS.) or (("257/342").CCLS.) or (("257/401").CCLS.) or (("257/135").CCLS.) or (("257/491").CCLS.) or (("257/492").CCLS.) or (("257/493").CCLS.)) and (trench or groove) and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 16:41
-	166	((("257/341").CCLS.) or (("257/342").CCLS.) or (("257/401").CCLS.) or (("257/135").CCLS.) or (("257/491").CCLS.) or (("257/492").CCLS.) or (("257/493").CCLS.)) and (trench or groove) and gate and power adj2 (semiconductor or device)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 16:43
-	65	((("257/341").CCLS.) or (("257/342").CCLS.) or (("257/401").CCLS.) or (("257/135").CCLS.) or (("257/491").CCLS.) or (("257/492").CCLS.) or (("257/493").CCLS.)) and (trench or groove) and gate and power adj2 (semiconductor or device) and trench adj3 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 17:03

-	789	((("257/341") or ("257/342") or ("257/135"))).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 17:04
-	104	((("257/341") or ("257/342") or ("257/135"))).CCLS.) and ((groove or trench) near5 gate) and (power near5 (device or semiconductor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 17:06
-	48	((("257/341") or ("257/342") or ("257/135"))).CCLS.) and ((groove or trench) near5 gate) and (power near5 (device or semiconductor))) not (((("257/341").CCLS.) or ("257/342").CCLS.) or ("257/401").CCLS.) or ("257/135").CCLS.) or ("257/491").CCLS.) or ("257/492").CCLS.) or ("257/493").CCLS.) and (trench or groove) and gate and power adj2 (semiconductor or device) and trench adj3 gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 17:06
-	1776	((("257/341") or ("257/342") or ("257/135") or ("257/329") or ("257/330") or ("257/331") or ("257/332"))).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 17:55
-	186	((("257/341") or ("257/342") or ("257/135") or ("257/329") or ("257/330") or ("257/331") or ("257/332"))).CCLS.) and ((trench or groove) near3 gate) and (power adj3 (semiconductor or device)) and ("igbt" or mosfet or nmosfet or pmosfet or dmosfet or cmosfet or insulated adj gate adj field adj effect adj transistor or metal adj oxide adj silicon adj transistor or metal-oxide-silicon adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 18:13
-	186	((("257/341") or ("257/342") or ("257/135") or ("257/329") or ("257/330") or ("257/331") or ("257/332"))).CCLS.) and ((trench or groove) near3 gate) and (power adj3 (semiconductor or device)) and ("igbt" or mosfet or nmosfet or pmosfet or dmosfet or cmosfet or insulated adj gate adj field adj effect adj transistor or metal adj oxide adj silicon adj field adj effect or metal-oxide-silicon adj field adj effect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 18:39
-	98	blanchard.in. and semiconductor and (257/\$5.ccls. or 438/\$5.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 18:40
-	720363	(blanchard.in. and semiconductor and (257/\$5.ccls. or 438/\$5.ccls.)) and trench ajd2 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 18:40
-	13	(blanchard.in. and semiconductor and (257/\$5.ccls. or 438/\$5.ccls.)) and trench adj2 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/30 18:41
-	4	blanchard.in. and trench adj2 gate	EPO; JPO; DERWENT; IBM TDB	2001/10/31 12:40

-	25	blanchard.in. and trench	EPO; JPO; DERWENT; IBM TDB	2001/10/31 12:50
-	5	(blanchard.in. and trench) and parasitic	EPO; JPO; DERWENT; IBM TDB	2001/10/31 12:56
-	4141	common adj drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/31 13:08
-	13721	common adj source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/31 13:09
-	119	((common adj drain) or (common adj source)) and trench adj2 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/31 13:09
-	107	((common adj drain) or (common adj source)) and trench adj2 gate) and (257/\$5.ccls. or 438/\$5.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/31 13:24
-	20	((common adj drain) or (common adj source)) and trench adj2 gate) and (257/\$5.ccls. or 438/\$5.ccls.) and power.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/31 14:25
-	3	5756386.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/10/31 14:26